

**What is claimed is:**

1. A semiconductor device comprising:  
a substrate having a region to be irradiated  
with radiating rays, and  
5 a metal wring layer located on the substrate  
one of directly and indirectly,  
wherein the metal wring layer is made of a  
light metal,  
and wherein the metal wring layer located on  
10 the region to be irradiated with radiating rays is formed  
thinner than that formed on regions except for the region  
to be irradiated so as to reach the radiating rays to the  
region to be irradiated.
- 15 2. The semiconductor device in accordance with  
claim 1, wherein none of the metal wring layer is located  
on the region to be irradiated.
- 20 3. The semiconductor device in accordance with  
claim 2, wherein an insulation layer is located on the  
region to be irradiated.
- 25 4. The semiconductor device in accordance with  
claim 3, wherein the metal wring layer located on the  
regions except for the region to be irradiated is formed  
in a thickness so as not to provide any adverse effect on

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the regions except for the region to be irradiated.

5. A semiconductor device comprising:

a substrate having a region to be irradiated  
5 with radiating rays, and

a metal wiring layer located on the substrate,  
wherein the metal wiring layer is made of a  
light metal,

and the metal wiring layer is used as a mask for  
10 restricting penetration of the radiating rays into  
regions except for the region to be irradiated.

6. The semiconductor device in accordance with  
claim 5, the semiconductor device is an insulated gate  
15 bipolar transistor, and wherein the region to be  
irradiated is a positive-negative junction region where a  
parasitic diode is generated.

7. The semiconductor device in accordance with  
20 claim 5, wherein the semiconductor device is a metal  
oxide semiconductor field effect transistor, and wherein  
the region to be irradiated is a positive-negative  
junction region where a parasitic diode is generated.

8. A method for manufacturing a semiconductor  
25 device having a substrate, and a metal wiring layer

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located on the substrate, a region of the substrate being irradiated with radiating rays, the method comprising the steps of:

entirely forming the metal wiring layer,

5 removing the metal wiring layer located on the region to be irradiated, and

radiating the radiating rays using the metal wiring layer being remained as a mask.

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